

PRODUCT/PROCESS CHANGE NOTIFICATION PCN13482 – Additional information

STM32G0B0x, STM32G0B1x and STM32G0C1x 512K - product enhancement

MDG – General Purpose Microcontrollers Division (GPM)

What are the changes?

Changes described in table below:

STM32G0B0x STM32G0B1x STM32G0C1x	Current Cut1.0	New Cut1.1
Die revision Marking R	"A"	"Z"

Example: Marking on package UFQFPN 7X7X0.55 48L





How to order samples?

- For all samples request linked to this PCN, please: place a <u>Non-standard</u> sample order (choose Sample Non Std Type from pull down menu) •
- insert the PCN number "PCN13482" into the NPO Electronic Sheet/Regional Sheet •
- request sample(s) through Notice tool, indicating a single Commercial Product for each request •

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Reliability Evaluation Report MDG-MCD-RER1918

STM32G0Bx (467X66)

New product qualification

Ger	eral Information	Traceability		
Commercial Product	STM32G0Bx	Diffusion Plant:	TSMC Fab14, Taiwan	
Product Line:	467X66	Assembly Plant:	ASE KH, Taiwan JSCC, China	
Die revision:	467XXXZ (cut1.1)			
Product Description:	STM32G0 512Kbytes flash			
Package:	LQFP 14x14 100L LQFP 12x12 80L LQFP 10x10 64L LQFP 7x7 48L LQFP 7x7 32L UFQFPN 7x7 48L UFQFPN 5x5 32L UFBGA 7x7 100L UFBGA 5x5 64L WLCSP52	Relia	ability Assessment	
Silicon Technology:	TSMC Fab14 90ULL	Pass		
Division:	MDG-MCD	Fail		
Reliability Maturity Level:	20->W29	Investigation required		

Note: this report is a summary of the reliability trials performed in good faith by STMicroelectronics to evaluate the electronic device conformance to its specific mission profile. This report and its contents shall not be disclosed to a third party without previous written agreement from STMicroelectronics or under the approval of the author (see below).



Version	Date	Author	Function
1.0	22-Oct-2020	Philippe ADAM	MDG-MCD Q&R engineer
1.1	10-Dec-2020	Philippe ADAM	MDG-MCD Q&R engineer
1.2	26-Feb-2021	Philippe ADAM	MDG-MCD Q&R engineer
1.3	17-Sept-2021	Philippe ADAM	MDG-MCD Q&R engineer
1.4	17-June-2022	Philippe ADAM – Octavia NDJOYE-KOGOU	MDG-MCD Q&R engineers

APPROVED BY:

VERSION 1.0

Function	Location	Name	Date
Division Q&R Responsible	Grenoble	Dominique GALIANO	19-Nov-2020
Division Quality Manager	Rousset	Pascal NARCHE	19-Nov-2020

VERSION 1.1

Function	Location	Name	Date
Division Q&R Responsible	Grenoble	Dominique GALIANO	10-Dec-2020

VERSION 1.2

Function	Location	Name	Date
Division Q&R Responsible	Grenoble	Dominique GALIANO	16-Mar-2021

VERSION 1.3

Function	Location	Name	Date
Division Q&R Responsible	Grenoble	Dominique GALIANO	10-Sept-2021

VERSION 1.4

Function	Location	Name	Date
Division Q&R Responsible	Grenoble	Dominique GALIANO	23 –June–2022



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1 RELIABILITY EVALUATION OVERVIEW

1.1 **Objective**

The aim of this report is to present results of the reliability evaluation performed on STM32G0Bx - Die 467XXXZ

Product	Process / Package	Diffusion, Assembly plant	Option
STM32G0B1VET6	90ULL, LQFP 14x14 100L	TSMC Fab14, SC ASE TAIWAN	General Purpose (GP)
STM32G0B1MET6	90ULL, LQFP 12x12 80L	TSMC Fab14, JSCC	General Purpose (GP)
STM32G0B1RET6	90ULL, LQFP 10x10 64L	TSMC Fab14, JSCC	General Purpose (GP)
STM32G0B1RET6N	90ULL, LQFP 10x10 64L	TSMC Fab14, JSCC	Power Delivery (PD)
STM32G0B1CET6	90ULL, LQFP 7x7 48L	TSMC Fab14, JSCC	General Purpose (GP)
STM32G0B1CET6N	90ULL, LQFP 7x7 48L	TSMC Fab14, JSCC	Power Delivery (PD)
STM32G0B1KET6	90ULL, LQFP 7x7 32L	TSMC Fab14, JSCC	General Purpose (GP)
STM32G0B1KET6N	90ULL, LQFP 7x7 32L	TSMC Fab14, JSCC	Power Delivery (PD)
STM32G0B1CEU6	90ULL, UFQFPN 7x7 48L	TSMC Fab14, JSCC	General Purpose (GP)
STM32G0B1CEU6N	90ULL, UFQFPN 7x7 48L	TSMC Fab14, JSCC	Power Delivery (PD)
STM32G0B1KEU6N	90ULL, UFQFPN 7x7 32L	TSMC Fab14, JSCC	General Purpose (GP)
STM32G0B1KEU6N	90ULL, UFQFPN 7x7 32L	TSMC Fab14, JSCC	Power Delivery (PD)
STM32G0B1VEI6	90ULL, UFBGA 7x7 100L	TSMC Fab14, ASE TAIWAN	General Purpose (GP)
STM32G0B1REI6N	90ULL, UFBGA 7x7 100L	TSMC Fab14, ASE TAIWAN	Power Delivery (PD)
STM32G0B1NEY6TR	90ULL. WLCSP 52L	TSMC Fab14. ASE TAIWAN	General Purpose (GP)

Test vehicle is described here below:

Qualification is based on standard STMicroelectronics Corporate Procedures for Quality and Reliability, in full compliancy with the JESD-47 international standard

1.2 Reliability Strategy

The STM32G0Bx (Die 467) is based on STM32G0 product family, processed in TSMC90nm technology in FAB14 and qualified on other STM32 products:

STM32L486x (die 415):	RERMCD1112
STM32L433x (die 435):	RERMCD1424
STM32G0x (die 460):	RERMCD1602
STM32L496x (die 461):	RERMCD1521
STM32L452x (die 462):	RERMCD1526



The STM32G0Bx (Die 467) device is assembled in the following packages already qualified for this product family:

Package	Reference	Assy Plant / location
LQFP100 14x14	RERMCD1810	ASE KH / Taiwan
LQFP80 12x12	RERMCD1818	
LQFP64 10x10	RERMCD1621	JSCC /
LQFP48 7x7	RERMCD1621	China
LQFP32 7x7	RERMCD1621	
UFQFPN48 7x7	RERMCD1622 RERMCD1718	
UFQFPN32 5x5	RERMCD1622	
UFBGA100 7x7	RERMCD1901	
UFBGA64 5x5	RERMCD1901	ASE KH / Taiwan
WLCSP52 P0.4	RERMCD1909	

Based on these data, and according to "RELIABILITY TESTS AND CRITERIA FOR QUALIFICATION" specification (DMS 0061692), the following qualification strategy has been defined:

• Die Qualification:

The full die reliability trials are conducted on one lot cut1.0 in LQFP100 GP bonding option and an add-on trial on cut1.1

• Package Qualification:

All packages used for this product have been already or will be validated on TSMC 90nm technology through the STM32L4 and STM32G4 families. Because of the introduction of the flying bonding at ASE KH and with LQFP80 at JSCC, one reliability lot is planned for LQFP100 ASE KH and one for LQFP80 JSCC. One additional lot is planned for QFN48 JSCC to collect reliability data on QFN 7x7. One reliability lot is planned for WLCSP52 ASE KH.

The reliability test plan and result summary are presented in the following tables:



STM32G0Bx – Reliability Evaluation Report

Package	Body	Pitch	Package Code	Wire	Assy	Bonding Option	Trial
LQFP 100	14x14	0.5	1L	Gold	ASE KH	GP	1 reliability lot (including
							partial CA)
LQFP 80	12x12	0.5	15	Gold	JSCC	GP	I reliability lot (including
							partial CA)
1 OFP 64	10x10	0.5	5W/	Cold	ISCC	GP	ESD CDM
LQIT 04	TOXTO	0.5	511	Gold	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	PD	ESD CDM
	7.7	0.5	E D	Cald	ISCO	GP	ESD CDM
LQFP 40	/ X /	0.5	ac	Gold	JSCC	PD	ESD CDM
	77	0.5	Γ\/	Cald		GP	ESD CDM
LQFP 32	/X/	0.5	20	Gold	JSCC	PD	ESD CDM
						CD	1 reliability lot (including
UFQFPN 48	7x7	0.5	A0B9	Gold	JSCC	GP	partial CA)
						PD	ESD CDM
	EVE	0.5	A 0 D 0	Cold	ISCC	GP	ESD CDM
UFQFPN 52	222	0.5	AUDO	Gold	JSCC	PD	ESD CDM
UFBGA 100	5x5	0.5	A0C2	Gold	ASE KH	GP	ESD CDM and partial CA
UFBGA 64	5x5	0.5	A019	Gold	ASE KH	PD	ESD CDM
WLCSP 52	N.A	0.4	BOBG	N.A	ASE KH	GP	1 reliability lot (including partial CA)

Bonding options: GP, General Purpose or Legacy; PD, USB Power Delivery Note: In order to cover all I/O options, some additional ESD CDM trials have been planned on different package bonding option.

1.3 Conclusion

All reliability tests have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

According to good reliability tests results in line with validated product mission profile and reliability strategy, the qualification is granted for the STM32G0Bx – Die 467XXXA in LQFP100 ASE KH, LQFP80 JSCC, LQFP64 JSCC, LQFP48 JSCC, LQFP32 JSCC, UFQFPN48 JSCC, UQFN32 JSCC, UFBGA64 ASE KH, UFBGA100 ASE KH and WLCSP52 ASE KH.

Refer to Section 3.0 for reliability test results.



2 PRODUCT CHARACTERISTICS

2.1 Generalities

The STM32G0Bx device – die 467 – is the ultra-low-power microcontroller based on the highperformance ARM[®] Cortex[®]-M0+ 32-bit RISC core operating at a frequency of up to 64MHz For additional information concerning the product behavior, refer to STM32L4G0Bx datasheet.

2.2 Traceability

2.2.1 Wafer fab information

<u>Table 1</u>

FAB1 Wafer fab name / location T14F / TSMC Fab 14 Wafer fab name / location T14F / TSMC Fab 14 Wafer thickness (µm) 775 +/- 25 Silicon process technology 90nm eFlash Generic TSMC Number of masks 45 Die finishing front side (passivation) USG + NITRIDE, 1.75 µm materials/thicknesses USG + NITRIDE, 1.75 µm Die finishing back side Raw silicon Materials/thicknesses 3125x3190 Die pad size (X, Y) 123, 59 Sawing street width (X, Y) (µm) 80, 80 Metal 1 tan/Ta/CuSeed/Cu 0.310µm Metal 2 Tan/Ta/CuSeed/Cu 0.310µm Metal 5 Tan/Ta/CuSeed/Cu 0.310µm Metal 5 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.310µm Metal 7 AlCu 1.450µm Metal 7 AlCu 1.450µm Metal 7 AlCu 1.450µm Die over coating (material/thickness) No FIT level (Ea-0.7eV, C.L: 60%, 55°C) Z 3 FITS at qualification date -Alpha SER: 491 FIT/Mb Neutron SER is an estimated using a nominal flux of 0.001α/h/cm² <th>Wafer fab information</th> <th></th>	Wafer fab information				
Wafer fab name / locationT14F / TSMC Fab 14Wafer thickness (µm)775 +/- 25Silicon process technology90nm eFlash Generic TSMCNumber of masks45Die finishing front side (passivation) materials/thicknessesUSG + NITRIDE, 1.75 µmDie finishing back side Materials/thicknessesRaw siliconDie area (Stepping die size)3125x3190Die pad size (X, Y)123, 59Sawing street width (X, Y) (µm)80, 80Metal I tan/Ta/CuSeed/Cu 0.240µm Metal 2 Tan/Ta/CuSeed/Cu 0.310µm Metal 5 Tan/Ta/CuSeed/Cu 0.310µm Metal 5 Tan/Ta/CuSeed/Cu 0.310µm Metal 6 Tan/Ta/CuSeed/Cu 0.310µm Metal 7 aN/Ta/CuSeed/Cu 0.3	FAB1				
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Die pad size (X, Y)123, 59Sawing street width (X, Y) (µm)80, 80Metal 1 TaN/Ta/CuSeed/Cu 0.240µm Metal 2 TaN/Ta/CuSeed/Cu 0.310µm Metal 3 TaN/Ta/CuSeed/Cu 0.310µm Metal 4 TaN/Ta/CuSeed/Cu 0.310µm Metal 5 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.350µm Metal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER (FIT/Mb) - Neutron SER (FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER: 445 FIT/Mb Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	Die area (Stepping die size)	3125x3190			
Sawing street width (X, Y) (μm)80, 80Metal 1 TaN/Ta/CuSeed/Cu 0.240μm Metal 2 TaN/Ta/CuSeed/Cu 0.310µm Metal 3 TaN/Ta/CuSeed/Cu 0.310µm Metal 3 TaN/Ta/CuSeed/Cu 0.310µm Metal 5 TaN/Ta/CuSeed/Cu 0.310µm Metal 5 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.310µm Metal 7 AlCu 0.30µm Metal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER (FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	Die pad size (X, Y)	123, 59			
Metal 1 TaN/Ta/CuSeed/Cu 0.240µmMetal 2 TaN/Ta/CuSeed/Cu 0.310µmMetal 3 TaN/Ta/CuSeed/Cu 0.310µmMetal 3 TaN/Ta/CuSeed/Cu 0.310µmMetal 4 TaN/Ta/CuSeed/Cu 0.310µmMetal 5 TaN/Ta/CuSeed/Cu 0.310µmMetal 6 TaN/Ta/CuSeed/Cu 0.310µmMetal 6 TaN/Ta/CuSeed/Cu 0.30µmMetal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate- Alpha SER (FIT/Mb]- Neutron SER (FIT/Mb]- Neutron SER (FIT/Mb]- ConditionsWafer Level Reliability- Electro-Migration (EM)- Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI)- Hot Carrier Injection (HCI)- Negative Bias Thermal Instality (NBTI)- Stress Migration (SM)Other Device(s) using same processStm32L4x, STM32C4x product family 415, 435, 461, 462, 464, 468, 469, 470	Sawing street width (X, Y) (µm)	80, 80			
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Metal levels/Materials/ThicknessesMetal 3 TaN/Ta/CuSeed/Cu 0.310µmMetal 4 TaN/Ta/CuSeed/Cu 0.310µmMetal 5 TaN/Ta/CuSeed/Cu 0.310µmMetal 5 TaN/Ta/CuSeed/Cu 0.310µmMetal 6 TaN/Ta/CuSeed/Cu 0.350µmMetal 6 TaN/Ta/CuSeed/Cu 0.850µmMetal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error RateAlpha SER (FIT/Mb]- Alpha SER (FIT/Mb]Neutron SER: 491 FIT/Mb- Neutron SER (FIT/Mb]Neutron SER is an estimation at sea level of NYC (14n/h/cm²)- ConditionsNeutron SER is an estimated using a nominal flux of 0.001α/h/cm²Wafer Level ReliabilityFilectro-Migration (EM)- Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI)Yess- Hot Carrier Injection (HCI)Yess- Negative Bias Thermal Instability (NBTI)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470		Metal 2 TaN/Ta/CuSeed/Cu 0.310µm			
Metal levels/Materials/ThicknessesMetal 4 TaN/Ta/CuSeed/Cu 0.310µm Metal 5 TaN/Ta/CuSeed/Cu 0.310µm Metal 6 TaN/Ta/CuSeed/Cu 0.850µm Metal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER [FIT/Mb] - ConditionsAlpha SER: 491 FIT/Mb Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470		Metal 3 TaN/Ta/CuSeed/Cu 0.310µm			
Metal 5 TaN/Ta/CuSeed/Cu 0.310µmMetal 6 TaN/Ta/CuSeed/Cu 0.850µmMetal 6 TaN/Ta/CuSeed/Cu 0.850µmMetal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error RateAlpha SER (491 FIT/Mb- Alpha SER [FIT/Mb]Neutron SER: 445 FIT/Mb- Neutron SER [FIT/Mb]Neutron SER is an estimation at sea level of NYC (14n/h/cm²)- ConditionsAlpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level ReliabilityYes- Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI)Yes- Hot Carrier Injection (HCI)Yes- Negative Bias Thermal Instability (NBTI)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	Metal levels/Materials/Thicknesses	Metal 4 TaN/Ta/CuSeed/Cu 0.310µm			
Metal 6 TaN/Ta/CuSeed/Cu 0.850µm Metal 7 AlCu 1.450µmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER [FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER: 445 FIT/Mb Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)YesOther Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470		Metal 5 TaN/Ta/CuSeed/Cu 0.310µm			
Metal 7 AlCu 1.450μmDie over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER [FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER [FIT/Mb]- Neutron SER [FIT/Mb]Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470		Metal 6 TaN/Ta/CuSeed/Cu 0.850µm			
Die over coating (material/thickness)NoFIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER [FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER is AP1 FIT/Mb Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)YesOther Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470		Metal 7 AlCu 1.450µm			
FIT level (Ea=0.7eV, C.L: 60%, 55°C)2.3 FITs at qualification dateSoft Error Rate - Alpha SER [FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER; 445 FIT/Mb Neutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)YesOther Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	Die over coating (material/thickness)	No			
Soft Error Rate - Alpha SER [FIT/Mb]Alpha SER: 491 FIT/Mb Neutron SER [FIT/Mb]- Neutron SER [FIT/Mb]Neutron SER: 445 FIT/Mb- ConditionsNeutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001 \alpha/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)YesOther Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	FIT level (Ea=0.7eV, C.L: 60%, 55°C)	2.3 FITs at qualification date			
- Alpha SER [FIT/Mb]Neutron SER: 445 FIT/Mb- Neutron SER [FIT/Mb]Neutron SER is an estimation at sea level of NYC (14n/h/cm²)- ConditionsAlpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level ReliabilityAlpha result is estimated using a nominal flux of 0.001α/h/cm²- Electro-Migration (EM)Yes- Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI)Yes- Hot Carrier Injection (HCI)Yes- Negative Bias Thermal Instability (NBTI)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	Soft Error Rate	Alpha SER: 491 FIT/Mb			
- Neutron SER [FIT/Mb] - ConditionsNeutron SER is an estimation at sea level of NYC (14n/h/cm²) Alpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)YesOther Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	– Alpha SER [FIT/Mb]	Neutron SER: 445 FIT/Mb			
- ConditionsAlpha result is estimated using a nominal flux of 0.001α/h/cm²Wafer Level Reliability - Electro-Migration (EM) - Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) - Hot Carrier Injection (HCI) - Negative Bias Thermal Instability (NBTI) - Stress Migration (SM)YesOther Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	- Neutron SER [FIT/Mb]	Neutron SER is an estimation at sea level of NYC (14n/h/cm ²)			
Wafer Level Reliability- Electro-Migration (EM)- Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI)Yes- Hot Carrier Injection (HCI)- Negative Bias Thermal Instability (NBTI)- Stress Migration (SM)STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	- Conditions	Alpha result is estimated using a nominal flux of $0.001\alpha/h/cm^2$			
 Electro-Migration (EM) Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) Hot Carrier Injection (HCI) Negative Bias Thermal Instability (NBTI) Stress Migration (SM) Other Device(s) using same process STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470 	Wafer Level Reliability				
 Time Dependent Dielectric Breakdown (TDDB) or Gate Oxide Integrity (GOI) Hot Carrier Injection (HCI) Negative Bias Thermal Instability (NBTI) Stress Migration (SM) Other Device(s) using same process STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470 	- Electro-Migration (EM)				
or Gate Oxide Integrity (GOI) res - Hot Carrier Injection (HCI) - - Negative Bias Thermal Instability (NBTI) - - Stress Migration (SM) STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	- Time Dependent Dielectric Breakdown (TDDB)	Vec			
- Negative Bias Thermal Instability (NBTI) - Stress Migration (SM) Other Device(s) using same process STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	or Gate Oxide Integrity (GOI)	res			
- Stress Migration (SM) Other Device(s) using same process STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	- Negative Rias Thermal Instability (NRTI)				
Other Device(s) using same processSTM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468, 469, 470	- Stress Migration (SM)				
Other Device(s) using same process 469, 470		STM32L4x, STM32G4x product family 415, 435, 461, 462, 464, 468,			
	Other Device(s) using same process	469, 470			



2.2.2 Assembly information

Table 2

Assembly Information					
Package 1 - 1L LQFP 14x14 100L General Purp	ose (GP)				
Assembly plant name/location	ASE KH / Taiwan				
Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	375 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference/supplier	LF# A25516 / Sumitomo				
Die attach material type/supplier	GLUE EPOXY CRM 1076WA / Sumitomo				
Wire bonding material/diameter/supplier	Wire gold / 0.8 mil / Tanaka				
Molding compound material/reference/supplier	Resin Sumitomo / EME-G631SH / Sumitomo				
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3				
Package 2 - 9X LQFP 12x12 80L General Purpo	se (GP)				
Assembly plant name/location	JSCC / China				
Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	375 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference/supplier	LQ12 80L 208sq eff slot Etch LF JSCC / Mitsui				
Die attach material type/supplier	Epoxy 3230 / Ablestik				
Wire bonding material/diameter/supplier	Wire Gold / 0.8 mil / Heraeus				
Molding compound material/reference/supplier	Mold Sumitomo / Iow alpha EME-G631SHQ / Sumitomo				
Package Moisture Sensitivity Level (JEDEC J–STD020D)	MSL3				
Package 3 - 5W LQFP 10x10 64L General Purpo	ose (GP)				
Assembly plant name/location	JSCC / China				
Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	375 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference/supplier	LQ10 64L 207sq Eff slots STMP LF JSCC / Mistui				
Die attach material type/supplier	Epoxy R008-0005A / Musashi				
Wire bonding material/diameter/supplier	Wire Gold / 0.8 mil / Heraeus				
Molding compound material/reference / supplier	Mold Sumitomo / low alpha G631SHQ / Sumitomo				
Package Moisture Sensitivity Level (JEDEC J–STD020D)	MSL3				
Package 4 - 5W LQFP 10x10 64L Power Deliver	Package 4 - 5W LQFP 10x10 64L Power Delivery (PD)				
Assembly plant name / location	JSCC / China				



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Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	375 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference/supplier	LQ10 64L 207sq Eff slots STMP LF JSCC / Mitsui				
Die attach material type/supplier	R008-0005A / Musashi				
Wire bonding material/diameter/supplier	Gold Wire / 0.8 mil / Heraeus				
Molding compound material/reference/supplier	Mold Sumitomo / low alpha G631SHQ / Sumitomo				
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3				
Package 5 - 5B LQFP 7x7 48L General Purpose	(GP)				
Assembly plant name/location	JSCC / China				
Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	150 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference/supplier	LQFP48L 184sq Eff slots STMP LF JSCC / HDS				
Die attach material type/supplier	Epoxy 3230 / Ablestik				
Wire bonding material/diameter/supplier	Wire Gold / 0.8mil / Heraeus				
Molding compound material/reference/supplier	Mold Sumitomo / low alpha EME-G631SHQ / Sumitomo				
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3				
Package 6 – 5B LQFP 7x7 48L Power Delivery (PD)					
Assembly plant name / location	JSCC / China				
Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	150 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference/supplier	LQFP48L 184sq Eff slots STMP LF JSCC / HDS				
Die attach material type/supplier	Epoxy 3230 / Ablestik				
Wire bonding material/diameter/supplier	Wire Gold / 0.8mil / Heraeus				
Molding compound material/reference/supplier	Mold Sumitomo / low alpha EME-G631SHQ / Sumitomo				
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3				
Package 7 - 5V LQFP 7x7 32L General Purpose	(GP)				
Assembly plant name / location	JSCC / China				
Pitch (mm)	0.5				
Die thickness after back-grinding (µm)	375 +/-25				
Die sawing method	laser grooving + mechanical sawing				
Bill of Material elements					
Lead frame reference	LQ7 32L 184sq Eff slots STMP LF JSCC				



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Die attach material type/supplier	Epoxy 3230 / Ablestik
Wire bonding material/diameter	Wire Gold / 0.8mil
Molding compound material/reference/supplier	Mold Sumitomo / low alpha G631SHQ / Sumitomo
Package Moisture Sensitivity Level (JEDEC J–STD020D)	MSL3
Package 8 - 5V LQFP 7x7 32L Power Delivery (PD)
Assembly plant name / location	JSCC / China
Pitch (mm)	0.5
Die thickness after back-grinding (µm)	375 +/-25
Die sawing method	laser grooving + mechanical sawing
Bill of Material elements	
Lead frame reference	LQ7 32L 184sq Eff slots STMP LF JSCC
Die attach material type/supplier	Epoxy 3230 / Ablestik
Wire bonding material/diameter	Wire Gold / 0.8mil
Molding compound material/reference/supplier	Mold Sumitomo / Iow alpha G631SHQ / Sumitomo
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3
Package 9 - A0B9 UFQFPN 7x7 48L General Pu	rpose (GP)
Assembly plant name / location	JSCC / China
Pitch (mm)	0.5
Die thickness after back-grinding (µm)	150 +/-25
Die sawing method	laser grooving + mechanical sawing
Bill of Material elements	
Lead frame reference/supplier	Rough Cu LF UQFN48L 5.2sq Groove JSCC / HDS
Die attach material type/supplier	Glue EN4900GC / Hitachi
Wire bonding material/diameter/supplier	Wire Gold / 0.8mil / MKE
Molding compound material/reference/supplier	RESIN SUMITOMO / EME-G770 / Sumitomo
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3
Package 10 - A0B9 UFQFPN 7x7 48L Power De	livery (PD)
Assembly plant name / location	JSCC / China
Pitch (mm)	0.5
Die thickness after back-grinding (µm)	150 +/-25
Die sawing method	laser grooving + mechanical sawing
Bill of Material elements	
Lead frame reference/supplier	Rough Cu LF UQFN48L 5.2sq Groove JSCC/HDS
Die attach material type /supplier	Glue EN4900GC / Hitachi
Wire bonding material/diameter/supplier	Wire Gold / 0.8mil / MKE
Molding compound material/reference/supplier	RESIN SUMITOMO / EME-G770 / Sumitomo
Package Moisture Sensitivity Level (JEDEC J–STD020D)	MSL3



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Package 11 - A0B8 UFQFPN 5x5 32L General Purpose (GP)				
Assembly plant name / location	JSCC / China			
Pitch (mm)	0.5			
Die thickness after back-grinding (µm)	150 +/-10			
Die sawing method	laser grooving + mechanical sawing			
Bill of Material elements				
Lead frame reference/supplier	LF FOR UQFN 5x5 32L Sn PAD 3.1 MM SQ Groove / HDS			
Die attach material type/supplier	Glue EN4900GC / Hitachi			
Wire bonding material/diameter/supplier	Wire Gold / 0.8mil / MKE			
Molding compound material/reference/supplier	RESIN SUMITOMO / G770 / Sumitomo			
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3			
Package 12 - A0B8 UFQFPN 5x5 32L Power Del	ivery (PD)			
Assembly plant name / location	JSCC / China			
Pitch (mm)	0.5			
Die thickness after back-grinding (µm)	150 +/-10			
Die sawing method	laser grooving + mechanical sawing			
Bill of Material elements				
Lead frame reference/supplier	LF FOR UQFN 5x5 32L Sn PAD 3.1 MM SQ Groove / HDS			
Die attach material type/supplier	Glue EN4900GC / Hitachi			
Wire bonding material/diameter/supplier	Wire Gold / 0.8mil / MKE			
Molding compound material/supplier/reference	RESIN SUMITOMO / G770 / Sumitomo			
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3			
Package 13 - A0C2 UFBGA 7x7 100L General P	urpose (GP)			
Assembly plant name / location	ASE KH / Taiwan			
Pitch (mm)	0.5			
Die thickness after back-grinding (µm)	75 +/-10			
Die sawing method	laser grooving + mechanical sawing			
Bill of Material elements				
Substrate material/supplier/reference	SUBSTRATE ASE A28313			
Die attach material type(glue/film)/supplier	D/A Tape ABLESTICK ATB-125			
Wire bonding material/diameter/supplier	Wire gold / 0.8 mils/ FP2			
Balls metallurgy/diameter/supplier	SOLDER BALLS SN96.5 AG3.5% / 200 DIAM / SHENMAO			
Molding compound material/reference/supplier	Resin / G1250AAS ULA / KYOCERA			
Package Moisture Sensitivity Level (JEDEC J-STD020D)	MSL3			
Package 14 - A019 UFBGA 7x7 64L Power Deliv	very (PD)			
Assembly plant name / location	ASE KH / Taiwan			
Pitch (mm)	0.5			
Die thickness after back-grinding (µm)	75 +/-10			



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Die sawing method	laser grooving + mechanical sawing
Bill of Material elements	
Substrate material/reference/supplier	SUBSTRATE / A28314 / ASE
Die attach material/type(glue/film)/supplier	D/A Tape ABLESTICK ATB-125
Wire bonding material/diameter/supplier	Wire gold / 0.8 mils / FP2
Balls metallurgy/diameter/supplier	SOLDER BALLS SN96.5 AG3.5% / 200 DIAM / Taoyuan
Molding compound material/reference/supplier	Resin / G1250AAS ULA / KYOCERA
Package Moisture Sensitivity Level	MSL3
(JEDEC J-STD020D)	
Package 15 - BOBG WLCSP 52L General Purpose	e (GP)
Assembly plant name / location	ASE KH / Taiwan
Pitch (mm)	0.4
Die thickness after back-grinding (µm)	355 (+/-25)
Die sawing method	Laser groove + mechanical sawing
Bill of Material elements	
Balls metallurgy/diameter/supplier	Solder ball alloy SAC405 Diam 230um
Routing/Redistribution layer (RDL) material	RDL Copper 6um
PBO passivation material	Low temp polyimide passivation - LTC9320
Backside coating material/thickness	Backside coating PET film
Package Moisture Sensitivity Level (JEDEC J- STD020D)	MSL1

2.2.3 Reliability testing information

Table 3

Reliability Testing Information	
Reliability laboratory name / location	GRAL / ST Grenoble

<u>Note:</u> ST is ISO 9001 certified. This induces certification of all internal and subcontractor labs. ST certification document can be downloaded under the following link: <u>http://www.st.com/content/st_com/en/support/guality-and-reliability/certifications.html</u>



3 TESTS RESULTS SUMMARY

3.1 Lot Information

<u>Table 4</u>

Lot #	Diffusion Lot / Wafer ID	Die Revision (Cut)	Trace Code	Raw Line	Package	Note
					ASE KH	Die
1	9R009397/9	1.0	AA025002	E01L*467ESXA	LQFP 14x14 100L	reliability
					GP	assessment
					ASE KH	Package
2	9R009397 / 9	1.0	AA025002	E01L*467ESXA	LQFP 14x14 100L	reliability
					GP	assessment
					JSCC	Package
3	9R009397 / 4	1.0	GQ02628B	709X*467ESXA	LQFP 12x12 80L	reliability
					GP	assessment
					JSCC	ESD CDM
4	9R009397 / 3	1.0	GQ025282	705W*467ESXA	LQFP 10x10 64L	reliability
					GP	assessment
	00000007				JSCC	ESD CDM
5	98009597	1.0	GQ0282A9	715W*467ESXA	LQFP 10x10 64L	reliability
	/ 5				PD	assessment
					JSCC	ESD CDM
6	9R009397 / 4	1.0	GQ028294	705B*467ESXA	LQFP 7x7 48L	reliability
					GP	assessment
					JSCC	ESD CDM
7	9R009397 / 3	1.0	GQ03020X	715B*467ESXA	LQFP 7x7 48L	reliability
					PD	assessment
					JSCC	ESD CDM
8	9R009397 / 4	1.0	GQ029243	705V*467ESXA	LQFP 7x7 32L	reliability
					GP	assessment
					JSCC	ESD CDM
9	9R009397 / 7	1.0	GQ03020F	715V*467ESXA	LQFP 7x7 32L	reliability
					PD	assessment
					JSCC	Package
10	9R009397 / 5	1.0	GQ0272B9	70MI*467ESXA	UFQFPN 7x7 48L	reliability
					GP	assessment
					JSCC	ESD CDM
11	9R009397 / 6	1.0	GQ0292C8	71MI*467ESXA	UFQFPN 7x7 48L	reliability
					PD	assessment
					JSCC	ESD CDM
12	9R009397 / 6	1.0	GQ029223	70MG*467ESXA	UFQFPN 5x5 32L	reliability
					GP	assessment



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					JSCC	ESD CDM
13	13 9R009397 / 6 1.0		GQ0292C7	71MG*467ESXA	UFQFPN 5x5 32L	reliability
					PD	assessment
					ASE KH	ESD CDM &
14	9R009397 /10	10	AA029077	ΕΟΜΙ *467ΕςγΔ		partial CA
14	51005557710	1.0	AA023077			reliability
					Gr	assessment
					ASE KH	ESD CDM
15	9R009397 / 10	1.0	AA029076	E02I*467ESXA	UFBGA 5x5 64L	reliability
				PD		
16	9R009397 / 13	1.0	AA036199	E00E*467ESXA	ASE KH	Package
	,				WLCSP52	reliability
17	9R024461 / 18	1.0	AA043021	E00E*467XXXA	GP	assessment
					ASE KH	Die
18	9R113632 / 1	1.1	AA208102	E41L*467ESXZ	LQFP 14x14 100L	reliability
					GP	assessment

3.2 Test plan and results summary

Table 5 - ACCELERATED LIFETIME SIMULATION TESTS - LQFP 14x14 100L GP, ASE KH/Gold, cut 1.0

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
HTOL	JESD22 A108	T=125°C Duration= 1200H 3V6	1	77	77	Lot 1: 0/77	
ESD HBM	ANSI/ESDA/ JEDEC JS-001	1500 Ω, 100 pF 2kV class2	1	3	3	Lot 1: 0/3	
Latch Up	JESD78	130°C	1	3	3	Lot 1: 0/3	
EDR	JESD22–A117	10kcy EW @ 125°C then Storage HTB 150°C Duration 1500H	1	77	77	Lot 1: 0/77	
EDR	JESD22-A117	10kcy EW @ 25°C then Storage HTB 150°C Duration 168h	1	77	77	Lot 1: 0/77	
EDR	JESD22-A117	10kcy EW @ -40°C then Storage HTB 150°C Duration 168H	1	77	77	Lot 1: 0/77	



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ELFR	JESD22-A108	Ta=125°C	1	500	500	Lot 1: 0/500
	JESD74	Duration= 48hrs				
		3V6				

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 6 – ACCELERATED LIFETIME SIMULATION TESTS – LQFP 14x14 100L GP, ASE KH/Gold, cut 1.1

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
HTOL	JESD22 A108	T=125°C Duration= 168H 3V6	1	77	77	Lot 18: 0/77	
ESD HBM	ANSI/ESDA/ JEDEC JS-001	Ta = +25°C 1500 Ω, 100 pF 2kV class2	1	3	3	Lot 18: 0/3	
Latch Up	JESD78	130°C	1	3	3	Lot 18: 0/3	
ESD CDM	AEC Q100- 011, AEC Q101-005, JS- 002	Ta = +25°C 250V	1	3	3	Lot 18: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 7 – ACCELERATED ENVIRONMENT STRESS TESTS: LQFP 14x14 100L GP, ASE KH / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	250V	1	3	3	Lot 2: 0/3	
PC	J-STD-020	24h bake@125°C, MSL3 (192h@30C/60%RH) 3x Reflow simulation Peak Reflow Temp= 260°C	1	308	308	Lot 2: 0/308	
тс	JESD22-A104	Ta=-65/150°C Duration= 500cyc ⊠ After PC	1	77	77	Lot 2: 0/77	



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UHAST	JESD22-A118	Ta=130°C ,85% RH Duration= 96hrs ⊠ After PC	1	77	77	Lot 2: 0/77	
HTSL	JESD 22-A103	Ta=150°C Duration= 1000hrs ⊠ After PC	1	77	77	Lot 2: 0/77	
ТНВ	JESD 22-A101	Ta=85°C/85%RH VDD=3v6 Duration= 1000hrs ⊠ After PC	1	77	77	Lot 2: 0/77	

<u>Note</u>: Test method revision reference is the one active at the date of reliability trial execution

Table 8 - PACKAGE ASSEMBLY INTEGRITY TESTS: LQFP 14x14 100L GP, ASE KH / Gold

Test code	Method	Tests Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
CA	Construction Analysis including - Visual inspection - Sawing inspection - Pull test - Ball shear	Internal ST specification	1	50	50	Lot 2: 0/50	PASS

<u>Note</u>: Test method revision reference is the one active at the date of reliability trial execution

Table 9 – ACCELERATED ENVIRONMENT STRESS TESTS: LQFP 12x12 80L GP, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	250V	1	3	3	Lot 3: 0/3	
PC	J-STD-020	24h bake@125°C, MSL3 (192h@30C/60%RH) 3x Reflow simulation Peak Reflow Temp= 260°C	1	77	77	Lot 3: 0/308	



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тс	JESD22-A104	Ta=−65/150°C Duration= 500cyc ⊠ After PC	1	77	77	Lot 3: 0/77	
			1	77	77	Lot 2: 0/77	
UHASI	JESU22-ATT8	Duration= 96hrs	I	77	//	Lot 3: 0/77	
HTSL	JESD 22-A103	Ta=150°C Duration= 1000hrs ⊠ After PC	1	77	77	Lot 3: 0/77	
ТНВ	JESD 22-A101	Ta=85°C/85%RH VDD=3v6 Duration= 1000hrs ⊠ After PC	1	77	77	Lot 3: 0/77	

<u>Note</u>: Test method revision reference is the one active at the date of reliability trial execution

Table 10 – PACKAGE ASSEMBLY INTEGRITY TESTS: LQFP 12x12 80L GP, JSCC / Gold

Test code	Method	Tests Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
СА	Construction Analysis including – Visual inspection – Sawing inspection – Pull test – Ball shear	Internal ST specification	1	50	50	Lot 3: 0/50	PASS

Note: Test method revision reference is the one active at the date of reliability trial execution



Table 11 - ENVIRONMENT STRESS TESTS: LQFP 10x10 64L GP, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ 500V JEDEC JS-002	V	1	77	77	Lot 4: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 12 - ENVIRONMENT STRESS TESTS: LQFP 10x10 64L PD, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	250V	1	77	77	Lot 5: 0/3	

Table 13 – ENVIRONMENT STRESS TESTS: LQFP 7x7 48L GP, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	500V	1	77	77	Lot 6: 0/3	

Table 14 – ENVIRONMENT STRESS TESTS: LQFP 7x7 48L PD, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	500V	1	77	77	Lot 7: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 15 – ENVIRONMENT STRESS TESTS: LQFP 7x7 32L GP, JSCC / Gold

Test	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot	Comments:
code						Fail/S.S.	(N/A =Not Applicable)



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ESD	ANSI/ESDA/	500V	1	77	77	Lot 8: 0/3	
CDM	JEDEC JS-002						

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 16 – ENVIRONMENT STRESS TESTS: LQFP 7x7 32L PD, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	500V	1	77	77	Lot 9: 0/3	

<u>Note</u>: Test method revision reference is the one active at the date of reliability trial execution

Table 17 - ACCELERATED ENVIRONMENT STRESS TESTS: UFQFPN 7x7 48L GP, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	500V	1	77	77	Lot 10: 0/3	
PC	J-STD-020	24h bake@125°C, MSL3 (192h@30C/60%RH) 3x Reflow simulation Peak Reflow Temp= 260°C	1	77	77	Lot 10: 0/308	
тс	JESD22-A104	Ta=-65/150°C Duration= 500cyc ⊠ After PC	1	77	77	Lot 10: 0/77	
UHAST	JESD22-A118	Ta=130°C ,85% RH Duration= 96hrs ⊠ After PC	1	77	77	Lot 10: 0/77	
HTSL	JESD 22-A103	Ta=150°C Duration= 1000hrs ⊠ After PC	1	77	77	Lot 10: 0/77	



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ТНВ	JESD 22-A101	Ta=85°C/85%RH	1	77	77	Lot 10: 0/77	
		VDD=3v6					
		Duration = 1000hrs					
		🛛 After PC					

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 18 - PACKAGE ASSEMBLY INTEGRITY TESTS: UFQFPN 7x7 48L GP, JSCC / Gold

Test code	Method	Tests Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
СА	Construction Analysis including – Visual inspection – Sawing inspection – Pull test – Ball shear	Internal ST specification	1	50	50	Lot 10: 0/50	PASS

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 19 - ENVIRONMENT STRESS TESTS: UFQFPN 7x7 48L PD, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	500V	1	77	77	Lot 11: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 20 – ENVIRONMENT STRESS TESTS: UFQFPN 5x5 32L GP, JSCC / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	500V	1	77	77	Lot 12: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 21 – ENVIRONMENT STRESS TESTS: UFQFPN 5x5 32L PD, JSCC / Gold

Test	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot	Comments:
code						Fail/S.S.	(N/A =Not Applicable)



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ESD	ANSI/ESDA/	500V	1	77	77	Lot 13: 0/3	
CDM	JEDEC JS-002						

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 22 - ENVIRONMENT STRESS TESTS: UFBGA 7x7 100L GP, ASE KH / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ JEDEC JS-002	250V	1	77	77	Lot 14: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 23 - PACKAGE ASSEMBLY INTEGRITY TESTS: UFBGA 7x7 100L GP, ASE KH / Gold

Test code	Method	Tests Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
CA	Construction Analysis including – Visual inspection – Package dimensions	JESDB100/B108 Internal ST specification	1	50	50	Lot 14: 0/50	Pass

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 24 – ENVIRONMENT STRESS TESTS: UFBGA 5x5 64L PD, ASE KH / Gold

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
ESD CDM	ANSI/ESDA/ 50 JEDEC JS-002	00V	1	77	77	Lot 15: 0/3	

Note: Test method revision reference is the one active at the date of reliability trial execution

Table 25 - ACCELERATED ENVIRONMENT STRESS TESTS: WLCSP52 GP, ASE KH

	Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot	Comments:
							Fail/S.S.	(N/A =Not Applicable)



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ESD	ANSI/ESDA/	250V	1	77	77	Lot 16: 0/3	
CDM	JEDEC JS-002						
PC	J-STD-020	24h bake@125°C,	1	77	77	Lot 16: 0/308	
		MSL1 (168h@85C/85%RH)					
		3x Reflow simulation					
		Peak Reflow Temp= 260°C					
тс	JESD22-A104	Ta=-65/150°C	1	77	77	Lot 16:0/77	
		Duration= 500cyc					
		🛛 After PC					
<u> </u>							
UHAST	JESD22-A118	Ta=130°C ,85% RH	1	77	77	Lot 16:0/77	
		Duration= 96hrs					
		⊠ After PC					
HTSL	IESD 22-A103	Ta=150°C	1	77	77	Lot 16:0/77	
	J	Duration = 1000hrs	-				
		🗵 After PC					
тнв	JESD 22-A101	Ta=85°C/85%RH	1	77	77	Lot 17: 0/77	
		VDD=3v6					
		Duration = 1000hrs					
		🗆 After PC					

<u>Note</u>: Test method revision reference is the one active at the date of reliability trial execution

Table 26 – PACKAGE ASSEMBLY INTEGRITY TESTS: WLCSP52 GP, ASE KH

Test code	Method	Tests Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
CA	Construction Analysis including - Visual inspection - SEM - POA - Sawing inspection - Cross section	JESDB100/B108	1	50	50	Lot 16: 0/50	PASS

Note: Test method revision reference is the one active at the date of reliability trial execution



4 APPLICABLE AND REFERENCE DOCUMENTS

Reference	Short description					
JESD47	Stress-Test-Driven Qualification of Integrated Circuits					
SOP2.4.4	Record Management Procedure					
SOP2.6.2	Internal Change Management					
SOP2.6.7	Finished Good Maturity Management					
SOP2.6.9	Package & Process Maturity Management in BE					
SOP2.6.11	Program Management for Product Development					
SOP2.6.17	Management of Manufacturing Transfers					
SOP2.6.19	Front-End Technology Platform Development and Qualification					
DMS 0061692	Reliability Tests and Criteria for Product Qualification					
ANSI/ESDA	Electrostatic discharge (ESD) consitivity testing human hedy model (HPM)					
JEDEC JS-001	Lectostatic discharge (LSD) sensitivity testing numan body moder (HBM)					
ANSI/ESDA	Electrostatic discharge (ESD) sensitivity testing charge device model (ESD CDM)					
JEDEC JS-002						
JESD78	IC Latch-up test					
JESD 22-A108	Temperature, Bias and Operating Life					
JESD 22-A117	Endurance and Data retention					
JESD 22-A103	High Temperature Storage Life					
J-STD-020:	Moisture/reflow sensitivity classification for non-hermetic solid-state surface mount devices					
JESD22-A113:	Preconditioning of non-hermetic surface mount devices prior to reliability testing					
JESD22-A118:	Unbiased Highly Accelerated temperature & humidity Stress Test					
JESD22-A104:	Temperature cycling					
JESD22-A110:	Temperature Humidity Bake					
JESD 22B102:	Solderability test					
JESD22B100/B108:	Physical dimension					



5 GLOSSARY

Reference	Short description
HTOL	High Temperature Operating Life
EDR	Endurance and Data Retention
ELFR	Early Failure Rate
PC	Preconditioning (solder simulation)
ТНВ	Temperature Humidity Bias
тс	Temperature cycling
uHAST	Unbiased Highly Accelerated Stress Test
HTSL	High temperature storage life
DMS	ST Advanced Documentation Controlled system/ Documentation Management system
ESD HBM	Electrostatic discharge (human body model)
ESD CDM	Electrostatic discharge (charge device model)
LU	Latch-up
CA	Construction Analysis

6 REVISION HISTORY

Pavision	Author	Content	Approval List						
REVISION	Autio	description	Function	Location	Name	Date			
1.0	Philippo ADAM	Initial roloaco	Q&R Quality Manager	Grenoble	Dominique GALIANO	19-Nov-2020			
		initial release	Div. Quality Manager	Rousset	Pascal NARCHE	19-Nov-2020			
1.1	Philippe ADAM	Add LQFP80 JSCC, LQFP64 PD JSCC, LQFP48 PD JSCC, UFQFPN48 JSCC, UQFN32 JSCC & UFBGA64 ASE KH	Q&R Quality Manager	Grenoble	Dominique GALIANO	10-Dec-2020			
1.2	Philippe ADAM	Add UFBGA100 ASE KH	Q&R Quality Manager	Grenoble	Dominique GALIANO	16-Mar-2021			
1.3	Philippe ADAM	Add WLCSP52 ASE KH	Q&R Quality Manager	Grenoble	Dominique GALIANO	20-Sept-2021			
1.4	Philippe ADAM – Octavia NDJOYE– KOGOU	Cut 1.1 LQFP100 ASE KH	Q&R Quality Manager	Grenoble	Dominique GALIANO	23-June-2022			



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